

SEMINARS SEMINAIRES

Monday 5 to Wednesday 7 April

WORKSHOP ON MATERIALS SCIENCE WITH
RADIOACTIVE ISOTOPES – ISOLDE / CERN

Monday 5 April

at 09.00 hrs – Council Chamber
bldg 503, first floor

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|-------------|---|
| 09.00–09.30 | <i>Recent Radioactive Ion-Beams
Development of Interest for Materials
Science</i>
H. Ravn / CERN-ISOLDE |
| 09.30–10.00 | <i>Longlived Primary Radioisotopes of
Transition Metals and Non-Transition
Metals</i>
K. Freitag / University of Bonn |
| 10.00–10.30 | <i>Ion Implantation in Semiconductor
Technology</i>
L. Frey / Fraunhofer Gesellschaft AIS -
Erlangen |
| 10.30–11.00 | Coffee break |
| 11.00–11.30 | <i>Structural Investigation of Implantation
Damage in Semiconductors by Emission
Channeling</i>
S.G. Jahn / University of Konstanz |
| 11.30–12.00 | <i>Electrical Characterization of High
Energy Implants in Semiconductors</i>
R. Gwilliam / University of Surrey |
| 12.00–14.00 | Lunch |
| 14.00–14.30 | <i>New Isotopes for Perturbed Angular
Correlation Spectroscopy</i>
G. Correia / CERN-ISOLDE |
| 14.30–15.00 | <i>Surface Physics with Radioactive Ion
Beams</i>
H. Haas / HMI - Berlin |
| 15.00–15.30 | <i>Conversion Electron Mössbauer Spectro-
scopy Studies of Surfaces and Thin Films</i>
J. Korecki / University of Mining and
Metallurgy, Krakow |
| 15.30–16.00 | Coffee break |
| 16.00–16.30 | <i>Infrared Spectroscopy of Buried Ultrathin
SiO₂ - films by the Grazing - Internal-
Reflection / Transmission Technique</i>
R. Brendel / MPI FKF - Stuttgart |
| 16.30–17.00 | <i>The Theory of Rare-Earth Impurities in
Semiconductors</i>
Lannoo - I.E.M.N. - ISEN - Lille |
| 17.00–17.30 | <i>Impurities and Defects in CdTe and ZnTe
Semiconductors</i>
J.L. Pautrat / CENG - Grenoble |

Tuesday 6 April

at 09.00 hrs – Council Chamber
bldg 503, first floor

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| 09.00–09.30 | <i>Deep Level Point Defects in III-V
Semiconductors and their Structure</i>
A. Winnacker / University of Erlangen |
| 09.30–10.00 | <i>The Determination of Impurity Sites in
GaAs from Isotopic Structure Revealed in
Infrared Vibrational Spectra</i>
R.C. Newnan / Blackett Laboratory -
London |
| 10.00–10.30 | <i>The Densities of States of Substitutional
Tin and Germanium Impurities in GaAs,
GaP and InP Measured by Electron
Spectroscopy</i>
J. W. Petersen - Mikroelektronik Centret
of Denmark - Lyngby |
| 10.30–11.00 | Coffee Break |
| 11.00–11.30 | <i>Ion Implantation Problems in GaAs</i>
B. J. Sealy / University of Surrey |
| 11.30–12.00 | <i>Hydrogen Passivation of III-V
Semiconductors Studied by Perturbed
Angular Correlation Spectroscopy</i>
D. Forkel / CERN-ISOLDE / CERN |
| 12.00–14.00 | Lunch |

at 14.00 hrs – PS Seminar Room
bldg 6/2-024

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| 14.00–14.30 | <i>Diffusion of Metal Atoms in Amorphous
Silicon</i>
W. Frank / MPI FKF - Stuttgart |
| 14.30–15.00 | <i>Quasielastic Moessbauer Spectroscopy to
Determine the Diffusion Mechanism in
Intermetallic Phases</i>
G. Vogl / University of Wien |
| 15.00–15.30 | <i>Diffusion of Fe - Atoms via Interstitial
Lattice Positions observed by In-Beam
Moessbauer Spectroscopy</i>
R. Sielemann / HMI, Berlin |
| 15.30 - 16.00 | Coffee break |
| 16.00 - 17.30 | Guided tour at ISOLDE |

Wednesday April 7

at 08.30 hrs – Council Chamber
bldg. 503, first floor

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| 08.30–09.00 | <i>Determination of Defect Structures by
ESR/ENDOR</i>
J.R. Nicklas / Univ. Bergakademie
Freiberg |
| 09.00–09.30 | <i>Defects in Silicon : Identification and
Recombination</i>
B. Monemar / Linköping University |
| 09.30 - 10.00 | <i>Evidence for Vacancy Percolation in
Highly-Doped Silicon</i>
G. Weyer / University of Aarhus |